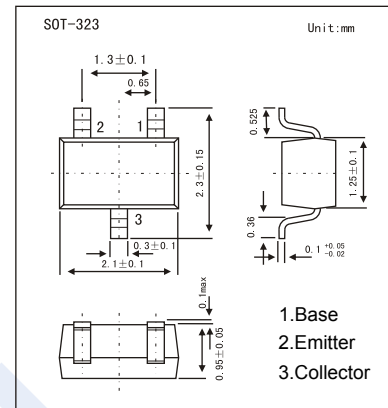


PNP Transistors

2SA1587

■ Features

- High voltage
- Low noise
- Complementary to 2SC4117
- Small Package



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-120	V
Collector - Emitter Voltage	V _{CE0}	-120	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _C	-100	mA
Base Current	I _B	-20	
Collector Power Dissipation	P _C	100	mW
Junction Temperature	T _J	125	°C
Storage Temperature range	T _{stg}	-55 to 125	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E = 0	-120			V
Collector- emitter breakdown voltage	V _{CE0}	I _C = -1 mA, I _B = 0	-120			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _C = 0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -120 V, I _E = 0			-0.1	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -5V, I _C = 0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -10 mA, I _B = -1 mA			-0.3	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C = -10 mA, I _B = -1 mA			-1.2	
DC current gain	h _{FE}	V _{CE} = -6V, I _C = -2mA	200		700	
Noise figure	NF	V _{CE} = -6V, I _C = 0.1mA, f = 1KHz, R _g = 10KΩ		1	10	dB
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		4		pF
Transition frequency	f _T	V _{CE} = -6V, I _C = -1mA		100		MHz

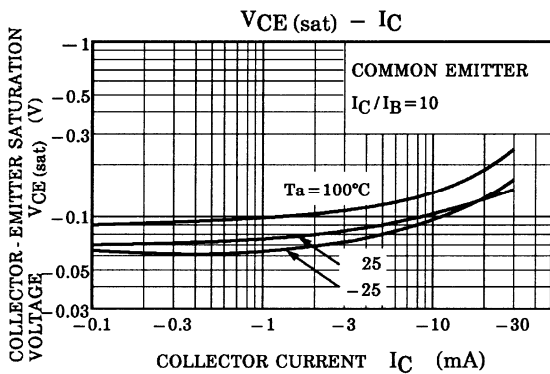
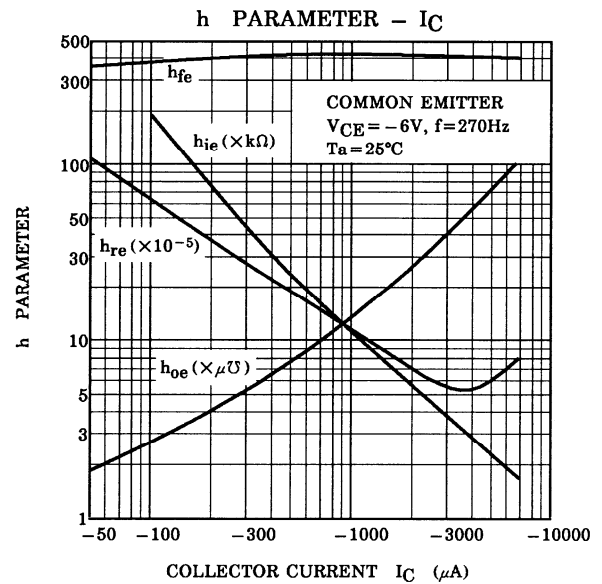
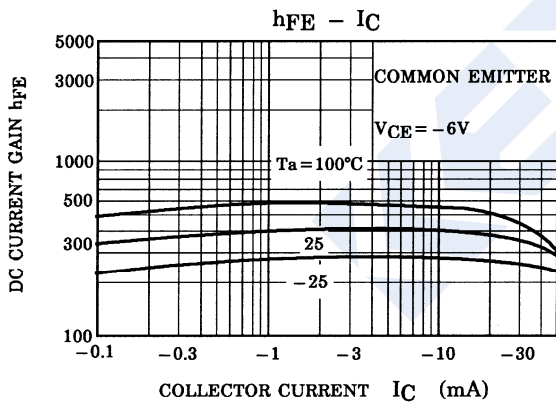
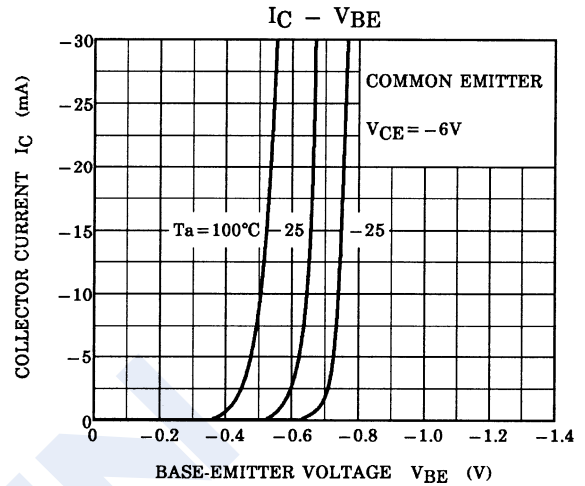
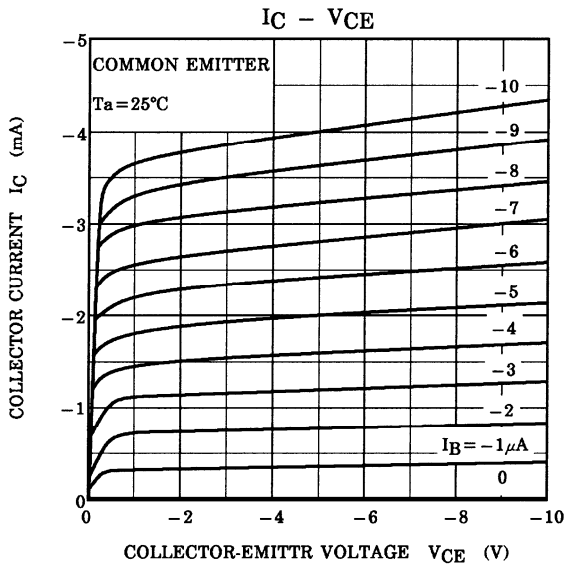
■ Classification of h_{FE}

Type	2SA1587-G	2SA1587-L
Range	200-400	350-700
Marking	CG	CL

PNP Transistors

2SA1587

■ Typical Characteristics



PNP Transistors

2SA1587

■ Typical Characteristics

